

TRANSISTOR (PNP)

FEATURES

- Low frequency power amplifier application
- Power switching application



MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current –Continuous	150	mA
P _C *	Collector Power Dissipation	100	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-0.1mA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-6V, I _C =-2mA	70		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-1mA,	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0 f=1MHz			7	pF
Noise Figure	NF	V _{CE} =-6V, I _C =-0.1mA f=1KHz, R _g =10KΩ			10	dB

CLASSIFICATION OF h_{FE}

Rank	O(2)	Y(4)	GR(6)
Range	70-140	120-240	200-400
MARKING	SO	SY	SG

Typical Characteristics



